#2

FORM PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET NO. **FIS920010105US1**	SERIAL NO. **Not Assigned** 09/899957
	APPLICANTS: James W. Adkisson, Michael J. Hargrove, Lyndon R. Logan, Isabel Y. Yang	
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U.S. PTO J1046 09/899957 07/06/01

REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS**

EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

MT		A. Yagishita et al.; "High Performance Metal Gate MOSFETs Fabricated by CMP for 0.1μm Regime"; 0-7803-4774-9/98, 1998 IEEE; IEDM 98-785; pgs. 29.3.1 - 29.3.4
MT		T. Matsuki et al.; "Cu/Poly-Si Damascene Gate Structured MOSFET with Ta and TaN Staked Barrier"; 0-7803-5410-9/99, 1999 IEEE; IEDM 99-261; pgs. 10.6.1 - 10.6.4
MT		A. Hiroki et al.; "A High Performance .01μm MOSFET with Asymmetric Channel Profile"; 0-7803-2700-4, 1995 IEEE; IEDM 95-439; pgs. 17.7.1 - 17.7.3
MT		A. Yagishita et al.; "High Performance Damascene Metal Gate MOSFETs for 0.1μm Regime"; 0018-9383/00, 2000 IEEE Transaction on Electron Devices, Vol. 47, No. 5; pgs. 1028-1034

EXAMINER Michael Trinh DATE CONSIDERED 9/30/02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.